PATENT ABSTRACTS OF JAPAN

(11) Publication number : 08-148658
(43) Date of publication of application : 07.06.1996

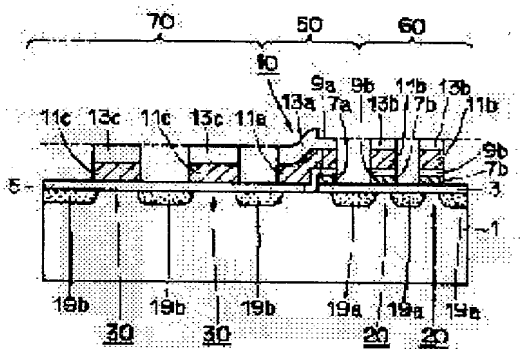
(51) Int.Cl. H01L 27/115
H01L 21/8247
H01L 29/788
H01L 29/792

(21) Application number : 06-285071
(22) Date of filing : 18.11.1994

(71) Applicant : MITSUBISHI ELECTRIC CORP
(72) Inventor : KUNORI YUUICHI

(54) SEMICONDUCTOR STORAGE DEVICE, AND ITS MANUFACTURE

(57) Abstract:
PURPOSE: To provide a semiconductor storage device suited to high integration and its manufacture.
CONSTITUTION: There are a memory transistor region 60, a selective transistor region 70, and a separating region 50 for separating these two regions, within a memory cell array. In the memory cell region 60 is a stack gate type of memory transistor 20 made. In the selective transistor region 70 is a selective transistor region 30 made. In the separating region 50 is a first conductive layer 7a made through an gate insulating layer 3 on a silicon substrate 1. On the upper surface and the side of the first conductive layer 7a is an interlayer insulating layer 9a made. Moreover, on the silicon substrate 1 are second conductive layer 11a and an insulating layer 13a stacked through a gate insulating layer 5 and besides so that they may ride on the first conductive layer 7a.



LEGAL STATUS

[Date of request for examination] 04.10.2000

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]